

Title (en)

SUBSTRATES INCLUDING A CAPPING LAYER ON ELECTRICALLY CONDUCTIVE REGIONS

Title (de)

SUBSTRATE MIT EINER KAPPENSCHICHT AUF ELEKTRISCH LEITFÄHIGEN REGIONEN

Title (fr)

SUBSTRATS COMPORTANT UNE COUCHE DE COUVERTURE SUR DES ZONES ELECTRIQUEMENT CONDUCTRICES

Publication

EP 1905072 A4 20101103 (EN)

Application

EP 06740290 A 20060403

Priority

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- US 13284105 A 20050518

Abstract (en)

[origin: WO2006124131A2] A masking layer is formed on a dielectric region of an electronic device so that, during subsequent formation of a capping layer on electrically conductive regions of the electronic device that are separated by the dielectric region, the masking layer inhibits formation of capping layer material on or in the dielectric region. The capping layer can be formed selectively on the electrically conductive regions or non-selectively. Capping layer material formed over the dielectric region can subsequently be removed, thus ensuring that capping layer material is formed only on the electrically conductive regions. The capping layer can be formed using appropriate processes.

IPC 8 full level

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Citation (search report)

- [X] US 2004213971 A1 20041028 - COLBURN MATTHEW E [US], et al
- [X] US 2004087176 A1 20040506 - COLBURN MATTHEW E [US], et al
- [A] US 2004248409 A1 20041209 - PADHI DEENESH [US], et al
- [A] US 2005001317 A1 20050106 - GANAPATHIRAMAN RAMANATH [US], et al
- [A] US 6323131 B1 20011127 - OBENG YAW SAMUEL [US], et al
- See references of WO 2006124131A2

Citation (examination)

US 2004250755 A1 20041216 - IVANOV IGOR C [US], et al

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